New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

PN4354
PN4355
PN4356

PNP SILICON TRANSISTOR

JEDEC TO-92 CASE (EBC)

MAXIMUM RATINGS ($T_A = 25^oC$)

	SYMBOL	PN4354 / PN4355	PN4356	UNITS
Collector-Base Voltage	V_{CBO}	60	80	V
Collector-Emitter Voltage	V_{CEO}	60	80	V
Emitter-Base Voltage	V_{EBO}	5.0	5.0	V
Collector Current	I_C	500	500	mA
Power Dissipation	P_D	625	625	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150		^oC
Thermal Resistance	θ_{JA}	200		$^oC/W$

ELECTRICAL CHARACTERISTICS ($T_A = 25^oC$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	PN4354 MIN	PN4354 MAX	PN4355 MIN	PN4355 MAX	PN4356 MIN	PN4356 MAX	UNITS
I_{CBO}	$V_{CB} = 50V$		50		50		50	nA
I_{CBO}	$V_{CB} = 50V$, $T_A = 75^oC$		5.0		5.0		5.0	μA
I_{EBO}	$V_{BE} = 4.0V$		100		100		100	nA
BV_{CBO}	$I_C = 10\mu A$	60		60		80		V
BV_{CEO}	$I_C = 10mA$	60		60		80		V
BV_{EBO}	$I_C = 10\mu A$	5.0		5.0		5.0		V
$V_{CE(SAT)}$	$I_C = 150mA$, $I_B = 15mA$		0.15		0.15		0.15	V
$V_{CE(SAT)}$	$I_C = 500mA$, $I_B = 50mA$		0.5		0.5		0.5	V
$V_{CE(SAT)}$	$I_C = 1.0A$, $I_B = 100mA$		-		1.0		-	V
$V_{BE(SAT)}$	$I_C = 150mA$, $I_B = 15mA$		0.9		0.9		0.9	V
$V_{BE(SAT)}$	$I_C = 500mA$, $I_B = 50mA$		1.1		1.1		1.1	V
$V_{BE(SAT)}$	$I_C = 1.0A$, $I_B = 100mA$		-		1.2		-	V
$V_{BE(ON)}$	$V_{CE} = 0.5V$, $I_C = 500mA$		1.1		1.1		1.1	V
$V_{BE(ON)}$	$V_{CE} = 1.0V$, $I_C = 1.0A$		-		1.2		-	V